

MOS FIELD EFFECT TRANSISTOR NP36N055HLE, NP36N055ILE

SWITCHING N-CHANNEL POWER MOS FET INDUSTRIAL USE

DESCRIPTION

These products are N-Channel MOS Field Effect Transistors designed for high current switching applications.

FEATURES

- Channel temperature 175 degree rated
- Super low on-state resistance
- ★ $R_{DS(on)1} = 13 \text{ m}\Omega \text{ MAX. (} V_{GS} = 10 \text{ V, } I_D = 18 \text{ A)}$
- ★ $R_{DS(on)2} = 16 \text{ m}\Omega \text{ MAX. (} V_{GS} = 5 \text{ V, } I_D = 18 \text{ A)}$
- ★ • Low C_{iss} : $C_{iss} = 2900 \text{ pF TYP.}$
- Built-in gate protection diode

ORDERING INFORMATION

PART NUMBER	PACKAGE
NP36N055HLE	TO-251(MP-3)
NP36N055ILE	TO-252(MP-3Z)

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Drain to Source Voltage	V_{DS}	55	V
Gate to Source Voltage	V_{GS}	± 20	V
Drain Current (DC)	$I_{D(DC)}$	± 36	A
Drain Current (Pulse) ^{Note1}	$I_{D(pulse)}$	± 144	A
Total Power Dissipation ($T_A = 25^\circ\text{C}$)	P_T	1.2	W
★ Total Power Dissipation ($T_C = 25^\circ\text{C}$)	P_T	120	W
★ Single Avalanche Current ^{Note2}	I_{AS}	36 / 33	A
★ Single Avalanche Energy ^{Note2}	E_{AS}	12 / 108	mJ
Channel Temperature	T_{ch}	175	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to + 175	$^\circ\text{C}$

Notes 1. $PW \leq 10 \mu\text{s}$, Duty cycle $\leq 1\%$

2. Starting $T_{ch} = 25^\circ\text{C}$, $R_G = 25 \Omega$, $V_{GS} = 20 \text{ V} \rightarrow 0 \text{ V}$

THERMAL RESISTANCE

★ Channel to Case	$R_{th(ch-C)}$	1.25	$^\circ\text{C/W}$
Channel to Ambient	$R_{th(ch-A)}$	125	$^\circ\text{C/W}$

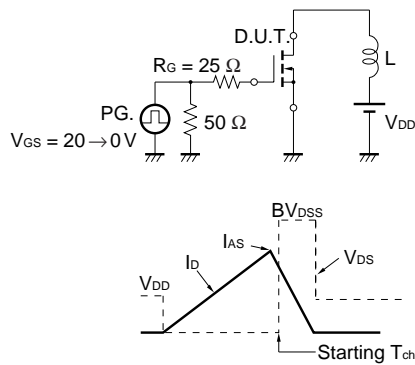
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Not all devices/types available in every country. Please check with local NEC representative for availability and additional information.

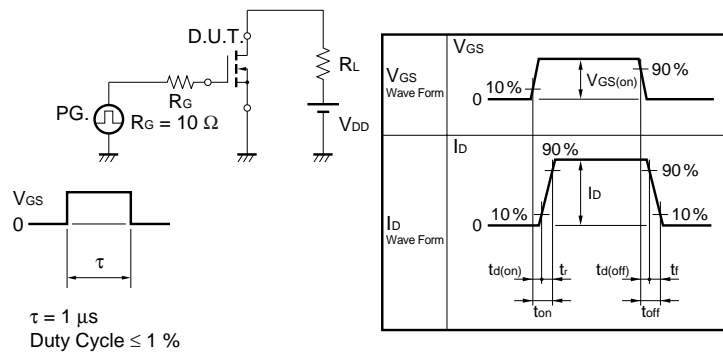
★ ELECTRICAL CHARACTERISTICS (T_A = 25 °C)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Drain to Source On-state Resistance	R _{DS(on)1}	V _{GS} = 10 V, I _D = 18 A		10	13	mΩ
	R _{DS(on)2}	V _{GS} = 5 V, I _D = 18 A		12	16	mΩ
	R _{DS(on)3}	V _{GS} = 4.5 V, I _D = 18 A		13	18	mΩ
Gate to Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1.5	2	2.5	V
Forward Transfer Admittance	y _{fs}	V _{DS} = 10 V, I _D = 18 A	11	23		S
Drain Leakage Current	I _{DSS}	V _{DS} = 55 V, V _{GS} = 0 V			10	μA
Gate to Source Leakage Current	I _{GSS}	V _{GS} = ±20 V, V _{DS} = 0 V			±10	μA
Input Capacitance	C _{iss}	V _{DS} = 25 V		2900	4400	pF
Output Capacitance	C _{oss}	V _{GS} = 0 V		370	560	pF
Reverse Transfer Capacitance	C _{rss}	f = 1 MHz		180	330	pF
Turn-on Delay Time	t _{d(on)}	I _D = 18 A		36	80	ns
Rise Time	t _r	V _{GS(on)} = 10 V		320	800	ns
Turn-off Delay Time	t _{d(off)}	V _{DD} = 28 V		130	260	ns
Fall Time	t _f	R _G = 10 Ω		120	300	ns
Total Gate Charge	Q _{G1}	I _D = 18 A		53	80	nC
	Q _{G2}	V _{DD} = 44 V		30	45	nC
Gate to Source Charge	Q _{GS}	V _{GS} = 10 V		9		nC
Gate to Drain Charge	Q _{GD}			15		nC
Body Diode Forward Voltage	V _{F(S-D)}	I _F = 36 A, V _{GS} = 0 V		1.0		V
Reverse Recovery Time	t _{rr}	I _F = 36 A, V _{GS} = 0 V		42		ns
Reverse Recovery Charge	Q _{rr}	di/dt = 100 A/μs		60		nC

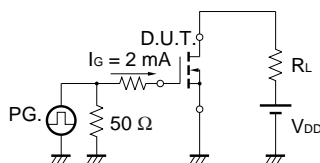
TEST CIRCUIT 1 AVALANCHE CAPABILITY



TEST CIRCUIT 2 SWITCHING TIME

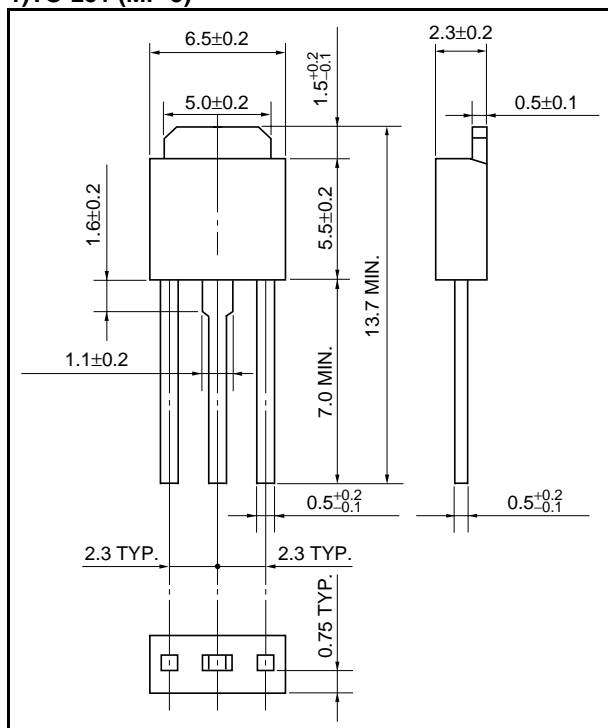


TEST CIRCUIT 3 GATE CHARGE

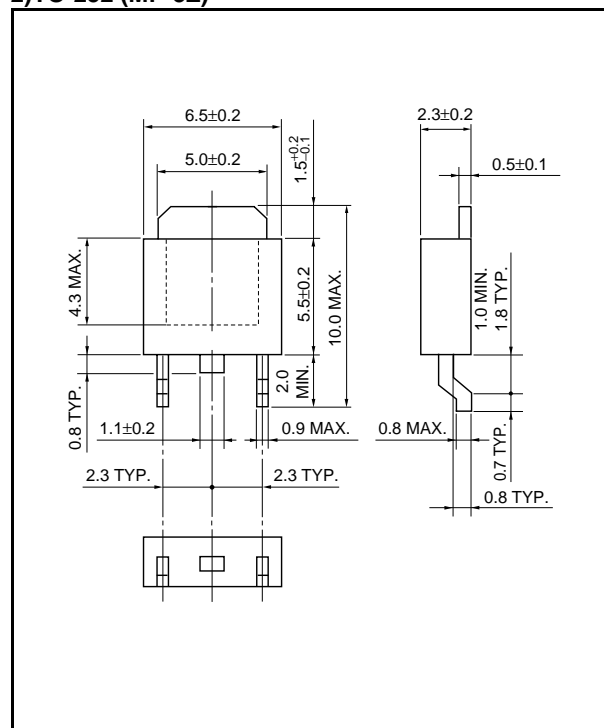


★ PACKAGE DRAWINGS (Unit : mm)

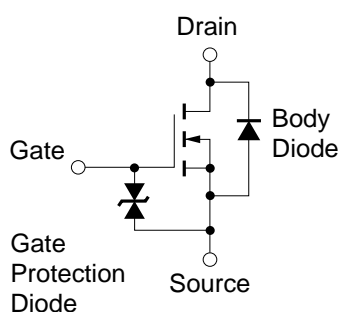
1)TO-251 (MP-3)



2)TO-252 (MP-3Z)



EQUIVALENT CIRCUIT



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD.

When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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